## Wire Bonding in Microelectronics

Materials, Processes, Reliability, and Yield

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Second Edition

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## Contents

Preface xi Acknowledgments xiv

Chapte	er 1. Te	chnical Introduction to the Second Edition	1	
1.1	Wedge	e- and Ball-Bonding Machine Operations	2	
1.2	How to Approach Bonding Problems			
	1.2.1	Which materials can be ultrasonically bonded?	6	
	1.2.2	Assessing the bondability and reliability of proposed		
		new bond systems	8	
	1.2.3	Some unusual uses of wire bonds	10	
		trasonic Bonding Systems and Technologies (Including re Bonding Mechanism)	11	
2.1	Introd	uction	11	
2.2	Ultras	onic Transducer and Tool Vibration Modes	11	
2.3	How L	Iltrasonic Bonds Are Made	18	
2.4	Bondi	ng with High (er) Frequency Ultrasonic Energy	23	
2.5		cess (Real-Time) Bond Monitoring	26	
2.6	Wire-Bonding Technologies		27	
	2.6.1	Thermocompression bonding	27	
	2.6.2	Ultrasonic wedge bonding (small- and large-diameter wires)	28	
	2.6.3	Thermosonic Ball and Wedge Bonding	29	
	2.6.4	Choosing a wire-bonding technology	30	
2.7	Variations of Fine Wire-Bonding Technology		30	
	2.7.1	Ribbon wire bonding	31	
	2.7.2	Parallel gap and tweezer welding	33	
2.8	Major	Major Chip Interconnection Alternatives to Wire Bonding		
	(Flip Chip and TAB); Limits of Wire Bonding		35	
2.9	Flip Chip			
	2.9.1	TAB	36	
	2.9.2	Wire-bonding technology: a comparison	37	

۷

		me Aspects of Bonding Wire Characteristics that nding, Reliability, and Testing	43	
3.1	Introd		43	
3.2		-Strain Characteristics of Bonding Wires	43	
3.3		Life Aging of Bonding Wires	45	
3.4		al Discussion of Gold Bonding Wire	50	
3.5		5	50	
		num Wire for Ultrasonic Wedge Bonding		
3.6		nd Metallization Hardness	53	
3.7		of EFO Polarity on Gold Wire and Its Metallurgy	54	
3.8		urgical Fatigue of Bonding Wires	55	
3.9		ictor Burnout	58	
	3.9.1	Bonding wires	58	
	3.9.2	Maximum allowable current for PCB and MCM conductors	63	
		dix WM-1: A Listing of Useful ASTM Standards and ications on Bonding Wire and Bond Testing	63	
Chapte	er 4. Wi	re Bond Testing	67	
4.1	Introd	uction	67	
4.1		estructive Bond Pull Test	67	
4.2	4.2.1	Variables of the bond pull test	68	
	4.2.2	Failure predictions that are based on pull test data	70	
	4.2.3	Effect of metallurgy and bonding processes on the		
		bond pull force	72	
	4.2.4	Effect of wire elongation on bond-pull force (large-		
		diameter AI, and Au wire used in ball bonding)	73	
4.3	Nonde	structive Pull Test	78	
	4.3.1	Introduction	78	
	4.3.2	Metallurgical and statistical interpretation of NDP test	79	
	4.3.3	Assessment of any NDP test-induced metallurgical		
	404	defects	81	
	4.3.4 4.3.5	Limitations of the NDP test The current status of the NDPT (1996) for military and	82	
	4.3.5	space applications	83	
4.4.	Ball-B	ond Shear Test	84	
4.4.		Introduction	84	
		Apparatus	85	
		A manual shear probe as an aid in setting up a ball		
		bonder	86	
	4.4.4	Interferences to making accurate ball-shear test		
		measurements	89	
		Ball-shear force versus bonded area	93	
		Effect of gold-aluminum intermetallics on the shear force	97	
		Pluck test	99	
	4.4.8 4.4.9	Comparison of the ball-shear and bond-pull tests Applications of the ball-shear test	99 100	
	4.4.10	••	105	
	4.4.11	Ball-shear test standardization	107	
4.5		ting Both the Ball and the Wedge Bond on a Single Wire	107	
4.6		Thermal Stress Test for Al-Au Wire Bond Reliability		
4.7	Future Issues in Wire Bond Testing		108 108	
4.8		dix TA-1	110	
4.0	Appen		110	

	<sup>5</sup> 5. Gold-Aluminum Intermetallic Compounds and Other Interface Reactions Encountered in Wire Bonding	115
5.1	Gold-Aluminum Intermetallic Compound Formation and	
	Classical Wire Bond Failures	115
	5.1.1 Introduction	115
	5.1.2 Intermetallic compound formation	116
	5.1.3 The classical Au-Al compound failure modes	122
	5.1.4 Reversing metallurgical interfaces	127
	5.1.5 The effect of diffusion inhibitors and barriers	128
5.2	Impurity-Accelerated Au-Al Bond Failures	129
	5.2.1 The effect of halogens on the Au-Al bond system	130
	5.2.2 Recommendations for removing or avoiding halogen contamination	134
	5.2.3 Nonhalogen epoxy outgassing induced bond failures	135
5.3	Non-gold-aluminum Bond Interfaces	135
	5.3.1 Aluminum-copper wire bond system	135
	5.3.2 Aluminum metallization containing copper	137
	5.3.3 Copper-gold wire bond system	138
	5.3.4 Palladium-Au and -Al bonding system (used for lead frames)	140
	5.3.5 The silver-aluminum wire bond system	142
	5.3.6 Aluminum-nickel wire bond system	144
	5.3.7 Au-Au, Al-Al, Au-Ag, and less-used monometallic	145
	bonding systems	
	Appendix IA-1:Rapid Bond Failure in Poorly Welded Au-Al Bonds	149
	Appendix IA-2:Various Bond-Related Corrosion Reactions	152
	6. Bond Failures Resulting from Gold-Plating Impurities	
and Co	nditions	161
6.1	Introduction	161
6.2	Specific Plating Impurities	163
6.3	Hydrogen Gas in Plated Films	165
	6.3.1 Hydrogen-induced package problems	170
	6.3.2 Failure symptoms that appear similar to gas	
	entrapments: resistance drift	170
6.4	Failures from Metallic impurities in or on Gold Films That Are	
	Not an Intentional Part of Plating Baths	171
	6.4.1 Introduction	171
	6.4.2 Nickel	173
	6.4.3 Copper	174
	6.4.4 Chromium	175
	6.4.5 Titanium	175
	6.4.6 Tin	176
6.5	Gold-Plating Standards	176
	6.5.1 Recommendations for reliable gold-plated films	176
6.6	Electroless Autocatalytic Gold	177
6.7	Nongold Platings Used in Electronics Packaging	178
Chapte	7. Cleaning to Improve Bondability and Reliability	181
7.1	Introduction	181
7.1	7.1.1 Molecular cleaning methods to enhance bondability	
	and reliability	184

	7.1.2 Ultraviolet-ozone cleaning 7.1.3 Plasma cleaning	185 187
	7.1.4 Plasma cleaning mechanism 7.1.5 Discussion and evaluation of molecular and solvent	190
	cleaning methods	192
	7.1.6 Problems encountered in using molecular cleaning methods	193
	7.1.7 Burnishing	195
7.2	The Sensitivity of Different Bonding Technologies to Surface Contamination	196
	Appendix CL-1: Circuit Damage Caused by Plasma Cleaning during Packaging	198
100	r 8. Mechanical Problems in Wire Bonding	203
8.1	Cratering	203
	8.1.1 Introduction	203
	8.1.2 Bonding machine characteristics and setup parameters	207
	8.1.3 Bonding force 8.1.4 Tool wire-pad impact force	208 209
	8.1.5 Causes of cratering—materials	210
	8.1.6 Intermetallics	213
	8.1.7 Silicon nodule-induced cratering	215
	8.1.8 Cratering over polysilicon	217
	8.1.9 Gallium arsenide cratering	219
8.2	Cracks in the Heels of Ultrasonic Wedge Bonds	223
8.3	The Effect of Acceleration, Vibrations, and Shock	226
	8.3.1 Centrifuge effects on wire bonds	226
	8.3.2 The effect of ultrasonic cleaning on wire bonds	228
	8.3.3 The effect of shock and vibration tests on wire bonds	231
8.4	Effects of Power and Temperature Cycling of Wire Bonds	231
	Appendix M-1: Fracture Toughness Defined	236
Chapte	r 9. High-Yield and Fine-Pitch Wire Bonding	241
9.1	Introduction	241
	The Background Necessary to Achieve High-Yield Bonding	242
9.3	The Requirements for High-Yield Bonding	243
0.0	9.3.1 Clean, bondable metallization	243
	9.3.2 The bonding machine and its control	247
9.4		248
9.5	· · · · · · · · · · · · · · · · · · ·	250
	Possible $6\sigma$ Yield Enhancements and Problems that Need	200
0.0	Further Study	251
9.7	The second se	253
	9.7.1 Wire sweep	253
	9.7.2 Wire looping	254
9.8	Fine-Pitch Ball and Wedge Bonding	255
	9.8.1 Introduction	255
	9.8.2 Fine-pitch ball and wedge bonding	255
9.9	The Problems of Fine-Pitch Bonding	257
9.10	Conclusions	259
9.11	Acknowledgments	260

Chapte	r 10. Wire Bonding to Multichip Modules and Other		
Soft Substrates		263	
10.1	Introduction	263	
10.2	Bonding to MCM-D Substrates	264	
10.3	Bonding to MCM-L Substrates	266	
10.4	The Effect of the Substrate's Material Properties on Wire Bonding	269	
10.5	Bonding Machine Considerations	274	
10.6	Additional Considerations When Using Wire Bonds in MCMs		
	Running at High Clock Rates	275	
	10.6.1 Inductance of wire bonds	275	
	10.6.2 Skin-effect in typical MCM conductor metal structures	276	
10.7	Conclusions	278	
10.8	Acknowledgments		

Glossary 281 Index 285